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(Not for submission under 37 CFR 1.99)

Application Number	10596726
Filing Date	2004-12-24
First Named Inventor	YANSON et al.
Art Unit	2828
Examiner Name	Not Yet Assigned
Attorney Docket Number	35832.000130

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		YI, H. et al., "Effect of dielectric and semiconductor cap layer combinations in impurity-free vacancy disordering of an InGaAs/InGaAsP single quantum well structure", Sae Mulli. Vol. 41, pp.193-8 (Sept. 2000) (Korean language version only available)	
	1	InGaAs/InGaAsP single quantum well structure", Sae Mulli. Vol. 41, pp.193-8 (Sept. 2000) (Korean language version only available)	<input type="checkbox"/>
	2	NG, S. et al., "Polarisation -dependent performance of multiple wavelength electro-absorption intensity modulator arrays on a single InGaAs/InGaAsP chip", LEOS, pp. 40 - 41 (2001)	<input type="checkbox"/>
	3	SU, Y. et al., "Effects of In _{0.53} /Ga _{0.47} cap layer and stoichiometry of dielectric capping layers on impurity-free vacancy disordering of In _{0.53} Ga _{0.47} /As/InP multiquantum well structures", J. Appl. Phys. 88:5720-3 (2000)	<input type="checkbox"/>
	4	NG, S. et al., "A low-cost solution in generating multiple-bandgaps for 1.55 μm optical fibre communications", IEEE Lasers and Electro Optics Soc. (LEOS), pp. 626-7 (2001)	<input type="checkbox"/>
	5	ONG, T. et al., "Fabrication of multiple-wavelength lasers in InGaAs-InGaAsP structures using direct laser writing", IEEE Photonics Technology Letters 13:1161-3 (Nov. 2001)	<input type="checkbox"/>
	6	ONG, T. et al., "Wavelength tuning in InGaAs/InGaAsP quantum well lasers using pulsed-photoabsorption-induced disordering", Appl. Phys. Letters 78:2637-9 (2001) ONG, T. et al., "Wavelength tuning in InGaAs/InGaAsP quantum well lasers using pulsed-photoabsorption-induced disordering", Appl. Phys. Letters 78:2637-9 (2001)	<input type="checkbox"/>
	7	SUDOH, T. et al., "Wavelength trimming of distributed-feedback lasers by photo-absorption-induced disordering", Conference Proceedings LEOS '96 9th Annual Meeting IEEE Lasers and Electro Optics Soc, pp. 419-20 (1996)	<input type="checkbox"/>
	8	Corrected Version of International Search Report by European Patent Office acting as ISA for International Application No. PCT/GB2004/005452, Mailed 12 August 2005.	<input type="checkbox"/>
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